

Pankaj Misra

List of Publications by Year in descending order

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119
papers

2,843
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136950

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214800

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119
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119
docs citations

119
times ranked

3522
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#	ARTICLE	IF	CITATIONS
1	Maxwellâ€“Wagner Relaxation-Driven High Dielectric Constant in Al ₂ O ₃ /TiO ₂ Nanolaminates Grown by Pulsed Laser Deposition. ACS Applied Materials & Interfaces, 2022, 14, 12873-12882.	8.0	13
2	Resistive switching characteristics of TiO ₂ thin films for nonvolatile memory applications. , 2022, , 413-451.		0
3	Studies on Resistive Switching of Cu/Ta ₂ O ₅ /Pt Devices for Non-volatile Memory Application. Springer Proceedings in Mathematics and Statistics, 2021, , 159-168.	0.2	0
4	Comment on â€œEnergy harvesting from shadow-effectâ€•by Q. Zhang, Q. Liang, D. K. Nandakumar, S. K. Ravi, H. Qu, L. Suresh, X. Zhang, Y. Zhang, L. Yang, A. T. S. Wee and S. C. Tan, <i>Energy Environ. Sci.</i>, 2020, 13, 2404. Energy and Environmental Science, 2021, 14, 4125-4129.	30.8	0
5	Observation of disorder induced weak localization in Gd:ZnO thin films. Physica B: Condensed Matter, 2021, 619, 413218.	2.7	1
6	Studies on structural, optical and electrical characteristics of zirconia thin films grown by pulsed laser deposition at different oxygen partial pressures. AIP Conference Proceedings, 2021, , .	0.4	0
7	Enhancing the Diode Characteristics of Pulsed Laserâ€“Deposited nâ€“Mg_xZn_{1â€“x}O/pâ€“Si Heterojunction: Role of Oxygen Ambient Pressure. Physica Status Solidi (A) Applications and Materials Science, 2020, 217, 2000440.	1.8	4
8	Low power high speed 3-bit multilevel resistive switching in TiO ₂ thin film using oxidisable electrode. Journal Physics D: Applied Physics, 2020, 53, 225303.	2.8	13
9	Disorder Driven Weak Localization and Phase Coherent Electron Transport in Ga Doped (Zn:V)O Thin Films. ECS Journal of Solid State Science and Technology, 2019, 8, Q61-Q65.	1.8	2
10	Studies on transient characteristics of unipolar resistive switching processes in TiO ₂ thin film grown by atomic layer deposition. Journal Physics D: Applied Physics, 2018, 51, 215101.	2.8	12
11	Comment on â€œStructural and Electrical Properties of Atomic Layer Deposited Alâ€“Doped ZnO Filmsâ€• Advanced Functional Materials, 2018, 28, 1702875.	14.9	3
12	Enhanced Sheet Charge Density in DIBS Grown CdO Alloyed ZnO Buffer Based Heterostructure. IEEE Electron Device Letters, 2018, 39, 827-830.	3.9	10
13	Observation of weak localization and phase coherent electron transport in sparsely doped (Zn:Ga)O thin films. Journal of Alloys and Compounds, 2017, 708, 73-78.	5.5	7
14	Epitaxial growth and band alignment properties of NiO/GaN heterojunction for light emitting diode applications. Applied Physics Letters, 2017, 110, .	3.3	27
15	Studies on dielectric, optical, magnetic, magnetic domain structure, and resistance switching characteristics of highly c-axis oriented NZFO thin films. Journal of Applied Physics, 2017, 122, 033902.	2.5	13
16	Investigating Optical Properties of Atomic Layer Deposited ZnO/TiO_x Multi-stacked Thin Films Above Mott Critical Density. Journal of Physical Chemistry C, 2017, 121, 18129-18136.	3.1	5
17	Studies on resistive switching times in NiO thin films grown by pulsed laser deposition. Journal Physics D: Applied Physics, 2017, 50, 415106.	2.8	19
18	Effect of growth temperature on diode parameters of n-ZnO/p-Si heterojunction diodes grown by atomic layer deposition. Materials Science in Semiconductor Processing, 2016, 54, 1-5.	4.0	32

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19	Dimensional crossover of electron weak localization in ZnO/TiO _x stacked layers grown by atomic layer deposition. Applied Physics Letters, 2016, 108, .	3.3	9
20	Resistive memory switching in ultrathin TiO ₂ films grown by atomic layer deposition. AIP Conference Proceedings, 2016, , .	0.4	8
21	Observation of dopant-profile independent electron transport in sub-monolayer TiO _x stacked ZnO thin films grown by atomic layer deposition. Applied Physics Letters, 2016, 108, .	3.3	11
22	UV light induced insulator-metal transition in ultra-thin ZnO/TiO _x stacked layer grown by atomic layer deposition. Journal of Applied Physics, 2016, 120, 085704.	2.5	7
23	Structural, electronic structure, and band alignment properties at epitaxial NiO/Al ₂ O ₃ heterojunction evaluated from synchrotron based X-ray techniques. Journal of Applied Physics, 2016, 119, .	2.5	26
24	Determination of band offsets at strained NiO and MgO heterojunction for MgO as an interlayer in heterojunction light emitting diode applications. Applied Surface Science, 2016, 389, 835-839.	6.1	11
25	Enhanced resistive switching in forming-free graphene oxide films embedded with gold nanoparticles deposited by electrophoresis. Nanotechnology, 2016, 27, 015702.	2.6	33
26	Resistive switching characteristics of mixed oxides. Emerging Materials Research, 2015, 4, 18-31.	0.7	2
27	Role of Al doping in structural, microstructural, electrical and optical characteristics of as-deposited and annealed ZnO thin films. RSC Advances, 2015, 5, 24178-24187.	3.6	23
28	Unipolar resistive switching in planar Pt/BiFeO ₃ /Pt structure. AIP Advances, 2015, 5, .	1.3	25
29	Band offset at TiO ₂ /MDMO PPV and TiO ₂ /PEDOT PSS interfaces studied using photoelectron spectroscopy. RSC Advances, 2015, 5, 97891-97897.	3.6	15
30	Observation of low resistivity and high mobility in Ga doped ZnO thin films grown by buffer assisted pulsed laser deposition. Journal of Alloys and Compounds, 2015, 638, 55-58.	5.5	41
31	Room temperature weak multiferroism and magnetodielectric effect in highly oriented (Y _{0.9} Bi _{0.1})(Fe _{0.5} Cr _{0.5})O ₃ thin films. Materials Research Bulletin, 2015, 68, 49-53.	5.2	7
32	Unipolar resistive switching behavior of high-k ternary rare-earth oxide LaHoO ₃ thin films for non-volatile memory applications. Materials Research Society Symposia Proceedings, 2015, 1729, 23-28.	0.1	1
33	Structural phase transition of ternary dielectric SmGdO ₃ : Evidence from angle dispersive x-ray diffraction and Raman spectroscopic studies. Journal of Applied Physics, 2015, 117, 094101.	2.5	9
34	Effects of electron interference on temperature dependent transport properties of two dimensional electron gas at MgZnO/ZnO interfaces. Applied Physics Letters, 2015, 107, .	3.3	10
35	Studies on magnetoelectric coupling in PFN-NZFO composite at room temperature. Journal of Applied Physics, 2014, 115, 194105.	2.5	27
36	Unipolar resistive switching behavior of amorphous YCrO ₃ films for nonvolatile memory applications. Journal of Applied Physics, 2014, 116, .	2.5	46

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37	Synchrotron based photoemission study on the band alignment and interface at ZnO/GaP hetero-junction. Applied Physics Letters, 2014, 104, 012109.	3.3	12
38	Growth of Sr ₂ FeMoO ₆ Based Tri-layer Structure for Room Temperature Magnetoresistive Applications. Integrated Ferroelectrics, 2014, 157, 89-94.	0.7	4
39	Multilevel unipolar resistive memory switching in amorphous SmGdO ₃ thin film. Applied Physics Letters, 2014, 104, 073501.	3.3	50
40	Properties of the new electronic device material LaGdO ₃ (Phys. Status Solidi B 1/2014). Physica Status Solidi (B): Basic Research, 2014, 251, n/a-n/a.	1.5	0
41	Effect of Poling on Photovoltaic Properties in Highly Oriented BiFeO ₃ Thin Films. Integrated Ferroelectrics, 2014, 157, 168-173.	0.7	6
42	Studies of the switchable photovoltaic effect in co-substituted BiFeO ₃ thin films. Applied Physics Letters, 2014, 105, .	3.3	35
43	Structural and Electrical Characteristics of Ternary Oxide SmGdO ₃ for Logic and Memory Devices. Materials Research Society Symposia Proceedings, 2014, 1633, 111-116.	0.1	2
44	Phase-coherent electron transport in (Zn, Al)Ox thin films grown by atomic layer deposition. Applied Physics Letters, 2014, 105, .	3.3	19
45	Multilevel resistive memory switching in graphene sandwiched organic polymer heterostructure. Carbon, 2014, 76, 341-347.	10.3	80
46	Enhanced photoresponse in BiFeO ₃ /SrRuO ₃ heterostructure. Journal of Alloys and Compounds, 2014, 609, 168-172.	5.5	25
47	Properties of the new electronic device material La _G dO ₃ . Physica Status Solidi (B): Basic Research, 2014, 251, 131-139.	1.5	13
48	Studies on highly resistive ZnO thin films grown by DC-discharge-assisted pulsed laser deposition. Applied Physics A: Materials Science and Processing, 2014, 114, 1119-1128.	2.3	6
49	Valence and conduction band offset measurements in Ni _{0.07} Zn _{0.93} O/ZnO heterostructure. Current Applied Physics, 2014, 14, 171-175.	2.4	33
50	Room temperature magnetoresistance in Sr ₂ FeMoO ₆ /SrTiO ₃ /Sr ₂ FeMoO ₆ trilayer devices. Journal Physics D: Applied Physics, 2014, 47, 065006.	2.8	20
51	Photovoltaic effect in transition metal modified polycrystalline BiFeO ₃ thin films. Journal Physics D: Applied Physics, 2014, 47, 075502.	2.8	54
52	Studies on structural, dielectric, and transport properties of Ni _{0.65} Zn _{0.35} Fe ₂ O ₄ . Journal of Applied Physics, 2014, 115, 243904.	2.5	102
53	Switchable photovoltaic effect in bilayer graphene/BiFeO ₃ /Pt heterostructures. Applied Physics Letters, 2014, 105, .	3.3	39
54	Tunneling electroresistance in multiferroic heterostructures. Nanotechnology, 2014, 25, 495203.	2.6	21

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55	Tunable Power Switching in Nonvolatile Flexible Memory Devices Based on Graphene Oxide Embedded with ZnO Nanorods. Journal of Physical Chemistry C, 2014, 118, 21357-21364.	3.1	63
56	Resistive Switching and Current Conduction Mechanisms in Amorphous LaLuO ₃ Thin Films Grown by Pulsed Laser Deposition. Integrated Ferroelectrics, 2014, 157, 47-56.	0.7	3
57	Spectroscopic ellipsometry characterization of amorphous and crystalline TiO ₂ thin films grown by atomic layer deposition at different temperatures. Applied Surface Science, 2014, 315, 116-123.	6.1	62
58	Polycrystalline Sr ₂ FeMoO ₆ thin films on Si substrate by pulsed laser deposition for magnetoresistive applications. Materials Letters, 2014, 118, 200-203.	2.6	11
59	Photoluminescence Processes in ZnO Thin Films and Quantum Structures. Springer Series in Materials Science, 2014, , 49-89.	0.6	1
60	Forming free resistive switching in graphene oxide thin film for thermally stable nonvolatile memory applications. Journal of Applied Physics, 2013, 114, 124508.	2.5	80
61	Effect of disorder on carrier transport in ZnO thin films grown by atomic layer deposition at different temperatures. Journal of Applied Physics, 2013, 114, 043703.	2.5	31
62	On the Resistive Switching and Current Conduction Mechanisms of Amorphous LaGdO ₃ Films Grown by Pulsed Laser Deposition. ECS Transactions, 2013, 53, 229-235.	0.5	10
63	Unipolar Resistive Switching and Associated Photoresponse in Sm doped BiFeO ₃ Thin Film Grown by RF Sputtering. Materials Research Society Symposia Proceedings, 2013, 1577, m1.	0.1	2
64	Nonvolatile Resistive Memory Switching in Amorphous LaGdO ₃ Thin Films. Materials Research Society Symposia Proceedings, 2013, 1562, 1.	0.1	0
65	Analysis of Leakage Currents through PLD Grown Ultrathin a-LaGdO ₃ Based High-k Metal Gate Devices. Materials Research Society Symposia Proceedings, 2013, 1561, 1.	0.1	0
66	Advanced high-k dielectric amorphous LaGdO ₃ based high density metal-insulator-metal capacitors with sub-nanometer capacitance equivalent thickness. Applied Physics Letters, 2013, 102, .	3.3	12
67	Advanced high-k gate dielectric amorphous LaGdO ₃ gated metal-oxide-semiconductor devices with sub-nanometer equivalent oxide thickness. Applied Physics Letters, 2013, 102, .	3.3	13
68	Effect of Mg diffusion on photoluminescence spectra of MgZnO/ZnO bi-layers annealed at different temperatures. Journal of Applied Physics, 2013, 114, 183103.	2.5	6
69	Band alignment and interfacial structure of ZnO/Ge heterojunction investigated by photoelectron spectroscopy. Applied Physics Letters, 2012, 101, .	3.3	25
70	Response to "Comment on "Room temperature photoluminescence from ZnO quantum wells grown on (0001) sapphire using buffer assisted pulsed laser deposition" [Appl. Phys. Lett. 101, 256101 (2012)]. Applied Physics Letters, 2012, 101, 256102.	3.3	0
71	Correlation of spectral features of photoluminescence with residual native defects of ZnO thin films annealed at different temperatures. Journal of Applied Physics, 2012, 112, .	2.5	48
72	Studies on temperature dependent semiconductor to metal transitions in ZnO thin films sparsely doped with Al. Journal of Applied Physics, 2012, 112, .	2.5	25

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73	Anomalous optical processes in photoluminescence from ultrasmall quantum dots of ZnO. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2011, 29, .	2.1	10
74	Correlation between electrical and optical properties of Cr:ZnO thin films grown by pulsed laser deposition. Physica B: Condensed Matter, 2011, 406, 4578-4583.	2.7	31
75	Synthesis and characterization of LaB6 thin films on tungsten, rhenium, silicon and other substrates and their investigations as field emitters. Applied Physics A: Materials Science and Processing, 2011, 104, 677-685.	2.3	19
76	Temperature-dependent photoluminescence of GaN grown on $\hat{1}^2$ -Si3N4/Si (111) by plasma-assisted MBE. Journal of Luminescence, 2011, 131, 614-619.	3.1	11
77	Growth temperature induced effects in non-polar a-plane GaN on r-plane sapphire substrate by RF-MBE. Journal of Crystal Growth, 2011, 314, 5-8.	1.5	16
78	Self-assembled flower-like nanostructures of InN and GaN grown by plasma-assisted molecular beam epitaxy. Bulletin of Materials Science, 2010, 33, 221-226.	1.7	17
79	Improved growth of GaN layers on ultra thin silicon nitride/Si (111) by RF-MBE. Materials Research Bulletin, 2010, 45, 1581-1585.	5.2	27
80	Structural, electrical and optical properties of Dy doped ZnO thin films grown by buffer assisted pulsed laser deposition. Physica E: Low-Dimensional Systems and Nanostructures, 2010, 42, 1838-1843.	2.7	40
81	Switching characteristics of ZnO based transparent resistive random access memory devices grown by pulsed laser deposition. Physica Status Solidi C: Current Topics in Solid State Physics, 2010, 7, 1718-1720.	0.8	23
82	Polarization Characteristics Variation of Visible Light on Reflection from ZnO Based Amorphous Films. Japanese Journal of Applied Physics, 2010, 49, 062602.	1.5	10
83	Studies on nonvolatile resistance memory switching in ZnO thin films. Bulletin of Materials Science, 2009, 32, 247-252.	1.7	36
84	Enhanced field emission from pulsed laser deposited nanocrystalline ZnO thin films on Re and W. Applied Physics A: Materials Science and Processing, 2009, 95, 613-620.	2.3	33
85	Temperature dependent photoluminescence processes in ZnO thin films grown on sapphire by pulsed laser deposition. Current Applied Physics, 2009, 9, 179-183.	2.4	34
86	Effect of Si doping on electrical and optical properties of ZnO thin films grown by sequential pulsed laser deposition. Journal Physics D: Applied Physics, 2009, 42, 165405.	2.8	99
87	Nano-Engineering by Implanting Al2O3 Nano Particle as Sandwiched Scattering Centers in Between the La0.5Pr0.2Sr0.3MnO3 Thin Film Layers. Journal of Nanoscience and Nanotechnology, 2009, 9, 5687-5691.	0.9	11
88	Enhanced field emission from LaB6 thin films with nanoprotusions grown by pulsed laser deposition on Zr foil. Applied Surface Science, 2008, 254, 3601-3605.	6.1	41
89	Nano - ZnO in Photonics Landscape. , 2008, , .		2
90	AMP activated protein kinase: a next generation target for total metabolic control. Expert Opinion on Therapeutic Targets, 2008, 12, 91-100.	3.4	105

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91	Some aspects of pulsed laser deposited nanocrystalline LaB ₆ film: atomic force microscopy, constant force current imaging and field emission investigations. Nanotechnology, 2008, 19, 265605.	2.6	30
92	Enhancement of electronic transport and magnetoresistance of Al ₂ O ₃ -impregnated (La _{0.5} Pr _{0.2})Sr _{0.3} MnO ₃ thin films. Europhysics Letters, 2007, 79, 17005.	2.0	13
93	Temperature dependent photoluminescence from ZnO/MgZnO multiple quantum wells grown by pulsed laser deposition. Superlattices and Microstructures, 2007, 42, 212-217.	3.1	12
94	Transparent p-AgCoO ₂ /n-ZnO diode heterojunction fabricated by pulsed laser deposition. Thin Solid Films, 2007, 515, 7352-7356.	1.8	62
95	Effects of swift heavy ion irradiation on La _{0.5} Pr _{0.2} Sr _{0.3} MnO ₃ epitaxial thin films grown by pulsed laser deposition. Nuclear Instruments & Methods in Physics Research B, 2007, 256, 693-697.	1.4	18
96	Field emission studies of pulsed laser deposited films on W and Re. Ultramicroscopy, 2007, 107, 825-832.	1.9	56
97	Field Emission from Nanocrystalline LaB ₆ Prepared by Laser Ablation. , 2006, , .		0
98	Structural, morphological, and electrical characterization of heteroepitaxial ZnO thin films deposited on Si (100) by pulsed laser deposition: Effect of annealing (800Å°C) in air. Journal of Applied Physics, 2006, 99, 014907.	2.5	18
99	Room temperature photoluminescence from ZnO quantum wells grown on (0001) sapphire using buffer assisted pulsed laser deposition. Applied Physics Letters, 2006, 89, 161912.	3.3	45
100	Development of a novel high optical quality ZnO thin films by PLD for III-V opto-electronic devices. Current Applied Physics, 2006, 6, 103-108.	2.4	64
101	Field emission studies on well adhered pulsed laser deposited LaB ₆ on W tip. Applied Physics Letters, 2006, 89, 123510.	3.3	52
102	A novel nano-architecture for ZnO thin films on Si, GaAs and InP single crystal wafers by L-MBE as value in nano-robotic (machining) device fabrication efforts. Materials Science in Semiconductor Processing, 2005, 8, 555-563.	4.0	9
103	Buffer-assisted low temperature growth of high crystalline quality ZnO films using Pulsed Laser Deposition. Thin Solid Films, 2005, 485, 42-46.	1.8	31
104	Optimized dual temperature pulsed laser deposition of TiO ₂ to realize MTOS (metal-TiO ₂ -SiO ₂ -Si) capacitors with ultrathin gate dielectric. Semiconductor Science and Technology, 2005, 20, 38-43.	2.0	6
105	Growth-parameters-dependent magnetoresistance in pulsed-laser-deposited (La _{0.5} Pr _{0.2})Ba _{0.3} MnO ₃ thin films. Journal of Applied Physics, 2005, 98, 086111.	2.5	5
106	Laser induced oxidation for growth of ultrathin gate oxide. Electronics Letters, 2004, 40, 1606.	1.0	4
107	Surface Modification of Tool Steel Using Tungsten Arc Heat Source. Surface Engineering, 2004, 20, 215-219.	2.2	7
108	Epitaxial lattice matching between epi-n-IZO thin films and ~100% Si, GaAs and InP wafers with out any buffer layers by L-MBE technique: a novel development for III-V opto-electronic devices. Materials Chemistry and Physics, 2004, 84, 14-19.	4.0	11

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109	Development of a novel high speed (electron-mobility) epi-n-ZnO thin films by L-MBE for III-V opto-electronic devices. Current Applied Physics, 2004, 4, 679-684.	2.4	7
110	Cluster formation in UV laser ablation plumes of ZnSe and ZnO studied by time-of-flight mass spectrometry. Applied Physics A: Materials Science and Processing, 2004, 78, 641-644.	2.3	62
111	Sequential pulsed laser deposition of CdxZn1-xO alloy thin films for engineering ZnO band gap. Applied Physics A: Materials Science and Processing, 2004, 78, 37-40.	2.3	44
112	Epi-n-IZO thin films/ $\sim 100\%$ Si, GaAs and InP by L-MBE—a novel feasibility study for SIS type solar cells. Solar Energy, 2004, 77, 193-201.	6.1	17
113	Nano-like magnesium oxide films and its significance in optical fiber humidity sensor. Sensors and Actuators B: Chemical, 2004, 98, 5-11.	7.8	108
114	Variable band gap ZnO nanostructures grown by pulsed laser deposition. Journal of Crystal Growth, 2004, 268, 531-535.	1.5	53
115	Epi-n-ZnO/ $\sim 100\%$ Si, GaAs and InP by L-MBE: a novel approach for III-V devices. Materials Science in Semiconductor Processing, 2003, 6, 219-224.	4.0	8
116	Alumina capped ZnO quantum dots multilayer grown by pulsed laser deposition. Solid State Communications, 2003, 127, 463-467.	1.9	25
117	Pulsed laser deposition of TiO2 for MOS gate dielectric. Applied Surface Science, 2002, 187, 297-304.	6.1	61
118	Study of iron nitride thin films deposited by pulsed laser deposition. Journal of Alloys and Compounds, 2001, 326, 265-269.	5.5	49
119	Variation of bandgap with oxygen ambient pressure in Mg _x Zn _{1-x} O thin films grown by pulsed laser deposition. Solid State Communications, 2001, 117, 673-677.	1.9	16